

Bilal Janjua

List of Publications by Year in descending order

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51
papers

1,396
citations

430874

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51
docs citations

51
times ranked

1583
citing authors

#	ARTICLE	IF	CITATIONS
1	Distributed feedback lasers using surface gratings in Bragg waveguides. <i>Optics Letters</i> , 2021, 46, 3689.	3.3	5
2	Timeâ€“Energy Quantum Uncertainty: Quantifying the Effectiveness of Surface Defect Passivation Protocols for Low-Dimensional Semiconductors. <i>ACS Applied Electronic Materials</i> , 2020, 2, 409-418.	4.3	4
3	Passively Mode-Locked Bragg Lasers With 64 GHz Sub-300 fs Pulses at 785 nm. <i>IEEE Photonics Technology Letters</i> , 2020, 32, 1135-1138.	2.5	4
4	Single-mode Bragg ring laser diodes. <i>Optics Letters</i> , 2020, 45, 2490.	3.3	4
5	Catalyst-Free Vertical ZnO-Nanotube Array Grown on p-GaN for UV-Light-Emitting Devices. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 27989-27996.	8.0	27
6	Functional integrity and stable high-temperature operation of planarized ultraviolet-A Al _x Ga _{1-<i>x</i>} N/Al _y Ga _{1-<i>y</i>} N multiple-quantum-disk nanowire LEDs with charge-conduction promoting interlayer. , 2019, , .		3
7	Ultraviolet-A LED Based on Quantum-Disks-In-AlGaN-Nanowiresâ€“Optimization and Device Reliability. <i>IEEE Photonics Journal</i> , 2018, 10, 1-11.	2.0	8
8	Surface-Passivated AlGaN Nanowires for Enhanced Luminescence of Ultraviolet Light Emitting Diodes. <i>ACS Photonics</i> , 2018, 5, 964-970.	6.6	67
9	Role of quantum-confined stark effect on bias dependent photoluminescence of N-polar GaN/InGaN multi-quantum disk amber light emitting diodes. <i>Journal of Applied Physics</i> , 2018, 123, .	2.5	20
10	Ultraviolet-A LED Based on Quantum-Disks-in-AlGaN-Nanowiresâ€“Optimization and Device Reliability. , 2018, , .		1
11	Quantified hole concentration in AlGaN nanowires for high-performance ultraviolet emitters. <i>Nanoscale</i> , 2018, 10, 15980-15988.	5.6	17
12	Tapering-induced enhancement of light extraction efficiency of nanowire deep ultraviolet LED by theoretical simulations. <i>Photonics Research</i> , 2018, 6, 457.	7.0	27
13	Diode junction temperature in ultraviolet AlGaN quantum-disks-in-nanowires. <i>Journal of Applied Physics</i> , 2018, 124, 015702.	2.5	11
14	Direct Growth of III-Nitride Nanowire-Based Yellow Light-Emitting Diode on Amorphous Quartz Using Thin Ti Interlayer. <i>Nanoscale Research Letters</i> , 2018, 13, 41.	5.7	17
15	Evolution of Junction Temperature and Heating Effects in UV AlGaN Nanowires LEDs. , 2018, , .		0
16	Ti/TaN Bilayer for Efficient Injection and Reliable AlGaN Nanowires LEDs. , 2018, , .		1
17	Health-friendly high-quality white light using violet-green-red laser and InGaN nanowires-based true yellow nanowires light-emitting diodes. , 2017, , .		3
18	Photoinduced entropy of InGaN/GaN p-i-n double-heterostructure nanowires. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	50

#	ARTICLE	IF	CITATIONS
19	Self-planarized quantum-disks-in-nanowires ultraviolet-B emitters utilizing pendeo-epitaxy. <i>Nanoscale</i> , 2017, 9, 7805-7813.	5.6	36
20	Spatially resolved investigation of competing nanocluster emission in quantum-disks-in-nanowires structure characterized by nanoscale cathodoluminescence. <i>Journal of Nanophotonics</i> , 2017, 11, 026015.	1.0	3
21	Nanomembrane-Based, Thermal Transport Biosensor for Living Cells. <i>Small</i> , 2017, 13, 1603080.	10.0	19
22	Enhancing the Light-Extraction Efficiency of an AlGa _N Nanowire Ultraviolet Light-Emitting Diode by Using Nitride/Air Distributed Bragg Reflector Nanogratings. <i>IEEE Photonics Journal</i> , 2017, 9, 1-8.	2.0	15
23	Thermodynamic photoinduced disorder in AlGa _N nanowires. <i>AIP Advances</i> , 2017, 7, .	1.3	12
24	Droop-free Al _x Ga _{1-x} N/Al _y Ga _{1-y} N quantum-disks-in-nanowires ultraviolet LED emitting at 337 nm on metal/silicon substrates. <i>Optics Express</i> , 2017, 25, 1381.	3.4	60
25	Highly uniform ultraviolet-A quantum-confined AlGa _N nanowire LEDs on metal/silicon with a TaN interlayer. <i>Optical Materials Express</i> , 2017, 7, 4214.	3.0	27
26	A Yellow Emitting InGa _N /Ga _N Nanowires-based Light Emitting Diode Grown on Scalable Quartz Substrate. , 2017, , .		0
27	Wireless optical transmission of 450 nm, 3.2 Gbit/s 16-QAM-OFDM signals over 6.6 m underwater channel. , 2016, , .		11
28	On the optical and microstrain analysis of graded InGa _N /Ga _N MQWs based on plasma assisted molecular beam epitaxy. <i>Optical Materials Express</i> , 2016, 6, 2052.	3.0	13
29	Droop-Free, Reliable, and High-Power InGa _N /Ga _N Nanowire Light-Emitting Diodes for Monolithic Metal-Optoelectronics. <i>Nano Letters</i> , 2016, 16, 4616-4623.	9.1	101
30	Synthesis of In _{0.1} Ga _{0.9} N/Ga _N structures grown by MOCVD and MBE for high speed optoelectronics. <i>MRS Advances</i> , 2016, 1, 1735-1742.	0.9	7
31	Determination of band offsets at Ga _N /single-layer MoS ₂ heterojunction. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	64
32	Bandgap measurements and the peculiar splitting of E _{2H} phonon modes of In _x Al _{1-x} N nanowires grown by plasma assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2016, 120, .	2.5	14
33	Ultrabroad linewidth orange-emitting nanowires LED for high CRI laser-based white lighting and gigahertz communications. <i>Optics Express</i> , 2016, 24, 19228.	3.4	20
34	True Yellow Light-Emitting Diodes as Phosphor for Tunable Color-Rendering Index Laser-Based White Light. <i>ACS Photonics</i> , 2016, 3, 2089-2095.	6.6	25
35	Facile Formation of High-Quality InGa _N /Ga _N Quantum-Disks-in-Nanowires on Bulk-Metal Substrates for High-Power Light-Emitters. <i>Nano Letters</i> , 2016, 16, 1056-1063.	9.1	84
36	Direct Growth of High-Power InGa _N /Ga _N Quantum-Disks-in-Nanowires Red Light-Emitting Diodes on Polycrystalline Molybdenum Substrates. , 2016, , .		0

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37	High-performance InGaN/GaN Quantum-Disks-in-Nanowires Light-emitters for Monolithic Metal-Optoelectronics. , 2016, , .		0
38	2 Gbit/s data transmission from an unfiltered laser-based phosphor-converted white lighting communication system. Optics Express, 2015, 23, 29779.	3.4	103
39	Achieving Uniform Carrier Distribution in MBE-Grown Compositionally Graded InGaN Multiple-Quantum-Well LEDs. IEEE Photonics Journal, 2015, 7, 1-9.	2.0	22
40	4-Gbit/s visible light communication link based on 16-QAM OFDM transmission over remote phosphor-film converted white light by using blue laser diode. Optics Express, 2015, 23, 33656.	3.4	87
41	Going beyond 4 Gbps data rate by employing RGB laser diodes for visible light communication. Optics Express, 2015, 23, 18746.	3.4	127
42	48 Gbit/s 16-QAM-OFDM transmission based on compact 450-nm laser for underwater wireless optical communication. Optics Express, 2015, 23, 23302.	3.4	266
43	Enhancement of Hole Confinement by Monolayer Insertion in Asymmetric Quantum-Barrier UVB Light Emitting Diodes. IEEE Photonics Journal, 2014, 6, 1-9.	2.0	3
44	Enhancing Carrier Injection Using Graded Superlattice Electron Blocking Layer for UVB Light-Emitting Diodes. IEEE Photonics Journal, 2014, 6, 1-12.	2.0	5
45	Optical Gain and Absorption of 420 nm InGaN-based Laser Diodes Grown on m-Plane GaN Substrate. , 2014, , .		0
46	Red to Near-Infrared Emission from InGaN/GaN Quantum-Disks-in-Nanowires LED. , 2014, , .		2
47	The formation of hexagonal-shaped InGaN-nanodisk on GaN-nanowire observed in plasma source molecular beam epitaxy. , 2014, , .		1
48	Extending quantum efficiency roll-over threshold with compositionally graded InGaN/GaN LED. , 2014, , .		0
49	Enhancing carrier injection in the active region of a 280nm emission wavelength LED using graded hole and electron blocking layers. Proceedings of SPIE, 2014, , .	0.8	0
50	Broadband back grating design for thin film solar cells. , 2013, , .		0
51	Increasing wavefunction overlap of carriers in an asymmetrically graded quantum well with polarization-effect-band-engineering.. , 2013, , .		0